# Sim ple model for scanning tunneling spectroscopy of noble metal surfaces with adsorbed K ondo im purities

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A simplem odel is introduced to describe conductancem easurements between a scanning tunneling microscope (STM) tip and a noblem etal surface with adsorbed transition metal atoms which display the K ondo elect. The model assumes a realistic parameterization of the potential created by the surface and a  $d_{3z^2}_{z^2}$  orbital for the description of the adsorbate. Fano lineshapes associated with the K ondo resonance are found to be sensitive to details of the adsorbate-substrate interaction. For instance, bringing the adsorbate closer to the surface leads to more asymmetric lineshapes while their dependence on the tip distance is weak. We not that it is important to use a realistic surface potential, to properly include the tunnelling matrix elements to the tip and to use substrate states which are orthogonal to the adsorbate and tip states. An application of our model to C o adsorbed on Cu explains the di erence in the lineshapes observed between Cu (100) and Cu (111) surfaces.

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#### I. IN TRODUCTION

The study of many-body phenomena in low dimensional systems is attracting a lot of attention. This has been motivated by recent advances in the construction of nanostructures and quantum dot devices. Scanning tunneling m icroscopy has also opened the possibility of analyzing many-body phenomena at surfaces. For instance, the K ondo e ect has been detected in STM conductance m easurements of noble metal surfaces with adsorbed 3d transition metal atom s.<sup>1,2,3,4,5</sup> Characteristic zero bias lineshapes are observed which are reminiscent of Fano<sup>6</sup> phenomena.

Fano lineshapes have been observed in di erent situations. They were rst explored by Fano<sup>6</sup> in his studies of autoionization of doubly excited He(2s2p) resonances lying in the continuum. In the case of adsorbed atom s on a metal surface an analogous situation is found as a localized orbital is also coupled to a continuum of m etallic states. As the adsorbate is magnetic, the K ondo e ect can occur and, therefore, Fano lineshapes can be thought of as arising from the interference of the K ondo resonance with the continuum of metal states.' It is worth noting that Fano phenom ena appears in STM measurem ents although the tip overlaps much more strongly with the surface than with the adsorbate wavefunctions (as the 3d orbitals are very localized) so that conductance m easurements re ect electronic properties of the metal surface m odied by the presence of the magnetic atom .

These Fano-type lineshapes di er from one adsorbate/substrate system to another, as sum marized in Table I, although som e experimental trends can be extracted. For instance, the Fano parameter, q, is typically either zero or positive. A s can be observed from the table the lineshape associated with q = 0 is a symmetric dip close to zero bias. The dependence of lineshapes may be illustrated by comparing the asymmetric dip observed for C o on C u (100) with the symmetric dip-like shape found for C o on C u (111). Similarly adsorbing T i instead of C o

TABLE I: N on-universality of lineshapes observed in conductance measurements between a STM tip and a noble metal surface with adsorbed 3d transition metal atom s and Ce. Depending on the adsorbate, the type of noble metal and/or the surface face, observed conductance lineshapes are dierent. The Fano parameter, q, which measures the degree of asymmetry of the lineshape associated with the K ondo resonance is typically q  $0. T_K$  denotes the associated K ondo temperatures given in degrees K elvin.

A dsorbate/Surface	$T_{\rm K}$ (K)	Type of lineshape	q	Ref.
Co/Cu(111)	54	nearly sym m etric dip	02	[2,3]
Co/Cu(100)	88	asym m etric dip	1.1	[3]
C o/A u (111)	75	asym m etric dip	0.6	[1]
T i/A u (111)	70	asym m etric dip+ peak	1	[8]
T i/A g (100)	40	asym m etric dip+ peak	1	[4]
Ce/Ag(111)	500	sym m etric dip	0	[5]
C o/A g (111)	92	sym m etric dip	0	[9]

on Au (111) leads to a strong variation of the lineshape. The situation becomes more complicated if we consider the "middle" elements of the 3d row which do not even show appreciable features in the conductance<sup>8</sup> down to T = 6 K. This raises questions about the occurrence of the K ondo e ect at all for these speci c adsorbates. Hence, experimental observations suggest that details associated with the adsorbate-substrate interaction m ay be relevant.

The Fano parameter, q, governing the shape of the conductance, G(!), close to zero bias, is given by:

$$q = \frac{A(F)}{B(F)}; \qquad (1)$$

where B (!) reads:

$$B (!) = M_{k}V_{k} (! _{k}); \qquad (2)$$

and, A (!), is the Kramers-Kronig transformation of

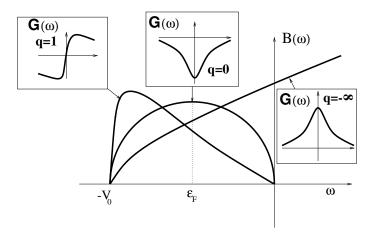


FIG.1: Correspondence of shape of B (!) with the Fano param eter. This schem atic plot gives a qualitative understanding of how the shape of the conductance, G (!), around the Ferm i energy is related to B (!). The Ferm i energy refered to the vacuum level is denoted by the dashed vertical line  $_{\rm F}$  = W, where W is the metalwork function. V<sub>0</sub> denotes the bottom of the band.

в (!):

A (!) = 
$$\frac{1}{2} \begin{bmatrix} Z & 1 \\ 1 & d! & 0 \\ 1 & 1 \end{bmatrix} \begin{bmatrix} 0 & (1 & 0) \\ 0 & (1 & 0) \end{bmatrix}$$
 (3)

In the above equations, M  $_k$  and V  $_k$  are the tip-substrate and adsorbate-substrate m atrix elements, respectively.  $_k$  is the substrate band dispersion and  $_F$  the position of the Ferm i level.

In order to understand the relation between the energy dependence of B (!) and the conductance lineshape we consider rst in Fig. 1 two di erent situations attending to the degree of asym metry of B (!): (i) B (!) is sym metric with respect to the Ferm ienergy. In this case, A ( $_{\rm F}$ ) = 0 and the Fano parameter, q = 0. Hence, the resulting conductance lineshape is a sym metric dip. (ii) B (!) is asym metric with most of its weight situated at frequencies below the Ferm ienergy ! <  $_{\rm F}$ . For this case, q > 0 and conductance lineshapes are more asym metric (q = 1 in the most asym metric lineshape). Hence, experimental observations requires that B (!) is in between cases (i) and (ii).

However, if we consider an sp-like band for the substrate and assume that hybridization matrix elements are independent of momentum, B (!) would be parabolic (from Eq. (2)), growing up to in nite energies. Due to the large asymmetry in B (!), A ( $_{\rm F}$ ) would be very large and negative so that q ! 1 leading to a peak (see Fig. 1) rather than the dip typically observed in experiments. Hence, it seems di cult to reconcile the observed conductance lineshapes with the shape of B (!) from this simplied picture. The question that we address in the present work is whether the momentum dependence of hybridization matrix elements can change B (!) leading to more symmetric conductance lineshapes. F irst attem pts to m odel the substrate electronic structure have been carried out by P lihal and G adzuk<sup>10</sup> who have used a Jellium m etal with a sharp step potential barrier at the surface. However, a half-lled symmetric density of states to describe the substrate (instead of parabolic) and momentum independent adsorbate-substrate hybridization m atrix elements, V<sub>k</sub>, were used. U nder these strong assumptions dip-like conductance lineshapes were obtained. T ight-binding descriptions of the substrate have also been used.<sup>11</sup> T hey provide a qualitative understanding of observations although their use is di cult to justify considering the sp free-like bands of noble m etal surfaces.

The above discussion shows the diculty of describing experim ental observations in a consistent way and points out the need of a more realistic model for describing the adsorbate-substrate-tip system.

An issue which needs to be carefully addressed in de ning the relevant m odel is to know which of the states associated with the surface (either surface and/orbulk states) are more strongly coupled to the adsorbate. There is experim ental evidence suggesting that surface states play only a minor role in the metal-adsorbate interaction<sup>3</sup>. For instance, the amplitude of the conductance decays rapidly as, G /  $1=R_{ii}^2$ , with lateral displacement of the tip, R  $_{\rm ii}$ , instead of decaying as 1=R  $_{\rm ii}$  expected for surface states coupled to the impurity. Furtherm ore, this bulklike behavior persists in conductance m easurem ents of C o on Cu (111), which is known to have a surface state at the Ferm i energy<sup>3</sup>. Based on the above experim ental observations we will only consider bulk states in our model. A nother experim ental observation is that lineshapes depend only weakly with perpendicular tip-substrate distance, Zt, suggesting that the direct interaction between the tip and the adsorbate is negligible<sup>12</sup>.

In the present work we show how using an Anderson m odel in an appropriate orthogonalized basis, reasonably symmetric shapes of B (!) are found which lead to conductance lineshapes in agreement with observations. We not that the momentum dependence of the hybridization matrix elements between the adsorbate  $3d_{3z^2} r^2$  orbital and the orthogonalized metal wavefunctions together with the nite size of the tip wavefunction are responsible for this behavior.

The present paper is organized as follows. In Section II we introduce an Anderson model in an orthogonalized basis to describe the adsorbate-substrate interaction together with the relevant formulas needed for discussing STM conductance measurements. In Section III we compute the parameters involved in the adsorbate-substrate interaction needed in the Anderson model. Section IV is devoted to describing the main results of our model. Finally, in Section V, we apply the model proposed to conductance measurements of C o atom s on noble metal surfaces.

# II. THEORETICAL APPROACH

In this section, details about the model used are given. An Anderson model on an orthogonal basis is considered. The parameters of the model are computed taking into account the following considerations: (i) Instead of a step barrier we consider a Jones-Jennings-Jepsen (JJJ) potential<sup>13</sup> to describe the metal surface wavefunctions, (ii) we neglect the direct coupling of the tip with the substrate d bands and with the 3d orbital of the adsorbate due to the localized nature of the d orbitals, (iii) the adsorbate is modelled by a single d-orbital, and (iv) the momentum dependence of the hybridization matrix elements is explicitly taken into account.

M etallic states,  $j_k >$ , coupled to a single  $d_{3z^2}_2$  orbital denoted by  $j_l$  > are considered. The Anderson m odel usually assumes that the optimum of m etal states are orthogonal to the localized orbitals of the adsorbate. However, the basis set form ed by the unperturbed m etal, adsorbate and tip wavefunctions,  $f_j > j_l > j_l > g$ , is non-orthogonal (in general) and overcom plete.

O neway to take into account orthogonalization e ects is to rede ne the metallic states, k, as:

$$\tilde{x} \ge k \ge \langle dk \ge jd \ge \langle dk \ge jz \ge (4)$$

C onsidering that tip and adsorbate wavefunctions are orthogonal:  $\langle tjl \rangle = 0$ , as  $jl \rangle$  is very localized, then the new m etallic states satisfy

$$\langle \tilde{K}j \rangle = 0;$$
 (5)

where j > can be either <math>t > or jd >.

O ur starting point is an Anderson model de ned in this new orthogonal basis: f $j\xi > ;jd > ;t > g$ , from which associated one-electron parameters,  $_R$ ,  $V_R$  and  $M_R$  are obtained. An analogous procedure was previously used in the context of chem isorption of atom s and molecules on m etal surfaces by G rim ley.<sup>14</sup>

It is worth m entioning that the new m etallic states are non-orthogonal am ong each other:

$$\langle \tilde{K}_{i} \hat{K}^{0} \rangle \in 0$$
: (6)

Hence, the orthogonalization condition between di erent  $\tilde{K} >$  states is violated. However, this occurs at higher order in the overlap: 0 (< k jd > <sup>2</sup>).

#### A. M odel

From the above considerations, our model for the com – plete tip-substrate system (with the 3d transition metal atom ) reads

$$H = H_{subs} + H_{tip subs} + H_{tip};$$
(7)

where H  $_{\rm subs}$  describes the substrate with the adsorbed 3d transition m etal atom and H  $_{\rm tip}$   $_{\rm subs}$  describes the interaction of the tip with the substrate. H  $_{\rm tip}$  describes the

tip which is assumed to have an unstructured density of states.

The substrate with the adsorbed 3d atom may be modelled by a generalized Anderson model that explicitly includes the orbital degeneracy of the 3d-orbital

Η

Here  $_{\rm d}$  is the energy level of an electron residing in the d orbital of the adsorbate,  $c_{\tt km}^y$  creates an electron with spin , momentum K and perpendicular projection of angular momentum, m, in the metal.  $d_{\tt m}^y$  creates an electron in the state with perpendicular projection of angular momentum m in the adsorbate.  $_{\tt K}$  and  $V_{\tt K}$  are the metallic energies and the hybridization matrix elements between the substrate and the adsorbate, respectively. U is the C oulomb repulsion of two electrons in the 3d orbital of the transition metal atom .

W e will restrict the sum to m = 0 as this is the orbital which is more strongly hybridized to the metallic surface.<sup>15</sup>. In this case, H am iltonian (8) reduces to the standard Anderson in purity model containing the spin degeneracy only.

Finally, the tip-substrate interaction contribution to the Ham iltonian reads

$$H_{tip subs} = \sum_{k;}^{X} M_{R} (c_{R}^{Y} t + H x:); \qquad (9)$$

through the matrix elements, M  $_{\rm g}$ . Here, t destroys an electron with spin in the tip.

#### B. Hybridization m atrix elements

In the following we describe how hybridization matrix elements, M  $_{\rm R}$  and V $_{\rm R}$ , are computed. For simplicity we will rst focus on how V $_{\rm R}$  is computed, as M $_{\rm R}$  is computed in a similar way.

Ignoring the electron-electron interaction we can reexpress H am iltonian (8) in rst quantized form

$$H_{subs} = T + V_d + V_M$$
; (10)

where T is the kinetic energy of the system,  $V_{\rm d}$  is the potential created by the adsorbate and  $V_{\rm M}$  describes the surface potential.

From Eqs. (4) and (10), the matrix elements between the orthogonalized metallic states, K, and the adsorbate read:

$$V_{\mathfrak{P}} = V_k \quad S_k < d \mathcal{Y}_M \quad \dot{\mathcal{J}}d > ; \tag{11}$$

where, again, we have assumed:  $\langle tjd \rangle = 0$ .

The rst term in Eq. (11) is the hybridization matrix element with the unperturbed wavefunctions k:

$$V_k = \langle k \mathbf{j} V_M \mathbf{j} \mathbf{d} \rangle; \tag{12}$$

and the second contains the overlap m atrix element

$$S_k = \langle k j d \rangle :$$
 (13)

The above orthogonalization procedure automatically selects the metal potential  $V_{\rm M}~$  in the hybridization matrix elements favouring the region close to or inside the metal in the integrations. This diers from hybridization matrix elements computed with the original wavefunctions as in that case integrations over the whole space are involved.

F inally we note that orthogonalization e ects enter the model through matrix elements only. O rthogonalization e ects on the substrate band energies can be shown to be of higher order in the overlap. Hence, we will assume  $r_{\rm g} = r_{\rm h}$  in the rest of the paper.

#### C. Computation of conductance

Following R ef. [12] and for the sake of clarity we derive the basic equations needed for the computation of the conductance through the STM. If we neglect any modi cation of the substrate due to the presence of the tip (this is reasonable considering the fact that the tip is typically at about 5 10 A above the metal surface), then the conductance measured by the STM reads:<sup>10,11,12</sup>

$$G(!) = \frac{4e^2}{h} tip((!) + (!)); \quad (14)$$

where

$$(!) = \underbrace{M}_{k} \underbrace{M}_{k} \underbrace{f}(!) \qquad (15)$$

is the conductance associated with the clean substrate (without the adsorbed 3d transition m etalatom) and  $_{\rm tip}$  is the density of states of the tip.

M odi cations of the tip-surface coupling induced by the presence of the adsorbate are given by

$$(!) = \operatorname{Im} \frac{X}{k_{k}k^{0}} \frac{M_{k}V_{k}}{! k i} G_{dd}(!) \frac{M_{k^{0}}V_{k^{0}}}{! k^{0} i} : \quad (16)$$

In Eq. (14), tip is the density of states of the tip.  $G_{dd}$  (!) describes the electronic properties of the 3d adsorbate in m ersed in them etallic continuum including the m any-body e ects such as the K ondo e ect induced by the on-site C oulom b interaction, U, inside the localized 3d orbital. is an analytical continuation parameter.

For convenience Eq. (16) is rewritten in the following way

$$(!) = \operatorname{Im} f(A(!) + iB(!))G_{dd}(!)(A(!) + iB(!))g$$
(17)

where B (!) is de ned in Eq. (2) and A (!) is the K ram ers-K ronig transform ation of B (!) given in Eq. (3) with the m atrix elements evaluated with the orthogonalized wavefunctions,  $j\bar{x} > .$  For the system s of interest here, A (!) and B (!) are real. Function B (!) embodies the inform ation concerning the tip-substrate-adsorbate system as it depends on the tip-adsorbate separation, R, the position of the adsorbate with respect to the plane of ions,  $Z_d$ , and the m etal potential described by  $V_M$  through the m atrix elements,  $V_R$  and M  $_R$ . In the present work we analyze how B (!) and (!) depend on these parameters.

From Eq. (17) we notice that the conductance can, in principle, have any kind of shape as a result of the interference of the adsorbate with the substrate continuum of states. In the following we will see how, in fact, Eq. (14) reduces to the well known Fano expression.

#### D. Fano form ula for conductance

For the sake of clarity we provide the Fano expression for the conductance which can be derived from Eqs. (14)-(17) (details can be found in Ref. [7]). First of all, the G reen's function of the 3d orbital is assumed to be known and to have the simple form

$$G_{dd}(!) = \frac{A_{d}}{!} + \frac{A_{U}}{!} + \frac{A_{U}}{!} + \frac{A_{K}}{!} + \frac{$$

The three terms appearing in Eq. (18) correspond to the singly occupied atom ic d level situated at  $_d$ , the K ondo peak situated at  $_K$  and the doubly occupied level,  $_d + U$  refered to the Fermi level,  $_F$ . is de ned as the half-width of the 3d in purity glue to its hybridizaton with the m etal surface: (!) =  $\int_{k} \int_{k} \int_{k}^{2} \int_{k}^{2} (! \ _{k}) \cdot A_{K} \cdot A_{d}$ , and  $A_{U}$  are spectral weights associated with the K ondo, the singly occupied and doubly occupied adsorbate, respectively.

G reens function  $G_{dd}$  (!) given by Eq. (18) describes a magnetic in purity coupled to a metallic host in the K ondo regime. In the next section, we will give the param eters relevant to the 3d in purities in noble metals used to model  $G_{dd}$  (!).

W e introduce Eq. (18) in Eq. (17) and de ne ~  $\frac{1}{T_K} = \frac{K}{T_K}$ . For energies, ! <  $T_K$  and in the K ondo regime, T <<  $T_K$ , the following Fano expression for the conductance is obtained:

G (!) = C (!) 
$$\frac{(q + \sim)^2}{1 + \sim^2}$$
 + D (!); (19)

where C (!) and D (!) have a weak dependence on ! and q denotes the Fano parameter given by Eq. (1). Hence, the shape of the conductance observed, G (!), in the STM is governed by the value of the Fano parameter, q. Fig. 1 explains qualitatively the relation between B (!) and conductance lineshapes. To conclude this section, we emphasize that Fano lineshapes arising in the present model are a consequence solely of the interference between metal and adsorbate waves. No direct coupling between the tip and the 3d adsorbate is taken into account (which in any case should be very sm all) norneeded to explain Fano phenomena. How ever, we will see below that the tip has, in fact, an im portant in uence on the nal shape of B (!) (and (!)) through the matrix elements, M  $_{\rm p}$ .

# III. DISCUSSION OF PARAMETERS AND MODELLING OF THE SYSTEM

From previous section it becomes clear that the shape of the conductance as a function of the bias measured by the STM depends on the parameters modelling the adsorbate-substrate-tip interaction entering B (!). Here we give details of how these parameters are obtained.

A. Surface potential and metal wavefunctions

A realistic and at the same time simple description of  $V_{\rm M}~$  is attained by using a JJJ potential.<sup>13</sup> This potential interpolates between the image potential at long distances and the potential inside the bulk. It provides a realistic description of the surface barrier potential being particularly useful in interpreting LEED and photoem ission data of noble m etal surfaces.^{13,16,17}

The JJJ potential contains three param eters that can be obtained from thing the potential to density functional calculations or experimental data. The surface potential is given (in Rydberg energy units) by:

$$V_{M} (Z) = \begin{cases} 8 & \frac{1}{2(Z - Z_{im})} (1 - e^{-(Z - Z_{im})}); Z > Z_{im}; \\ \vdots & \vdots & \vdots \\ \frac{V_{0}}{A e^{-(Z - Z_{im}) + 1}}; Z < Z_{im} \end{cases}$$
(20)

Here 
$$V_0$$
 is the depth of the bulk potential and controls  
the sharpness of the surface barrier potential. The pa-  
ram eters  $A = 2V_0 = 1$  and  $= V_0 = A$  are obtained by  
in posing the condition of continuity of the potential at  
 $Z = Z_{im}$  (see Ref. [13] for more details). Throughout  
the paper we refer the tip,  $Z_t$ , the adsorbate position,  
 $Z_d$ , and the in age plane position,  $Z_{im}$ , to the last plane  
of ions situated at a (see Fig. 2) and all energies are re-  
ferred to the vacuum level. The sharpness of the potential  
barrier experienced by the electrons inside the m etal is  
controlled by . For increasing , for instance, the po-  
tential becomes gradually sharper. As we will see below  
param eter turns out to play an important role in our  
m odel.

M etallic wavefunctions are obtained considering box quantization. We de ne a large box of side 2a, which describes the substrate enclosed by a larger box of side 2L, where the relative sizes of the boxes satisfy: L >> a(see Fig. 2). In practice it is su cient to take a=L = 0.3. The perpendicular dependence of the wavefunction is obtained from the integration of Schrödingers equation in the presence of the JJJ potential starting at distances of

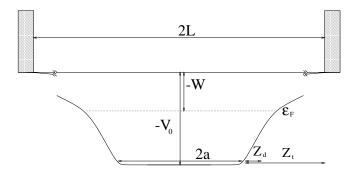


FIG. 2: Schem atic representation of the potential used to model the noble metal surface. The sizes of the large and small boxes used for quantization of the wavefunctions are given by 2L and 2a, respectively. The hatched vertical rectangles denote walls of in nite potential. Z<sub>d</sub> and Z<sub>t</sub> denote the positions of the adsorbate and the tip with respect to the last plane of ions. V<sub>0</sub> is the height of the surface barrier and W the metal workfunction. The Ferm i energy is referred to the vacuum leveland is denoted by the horizontal dotted line: F = W

about 25 A outside the surface towards them etal. Im posing periodic boundary conditions in the parallel direction, the crystal wavefunction reads:

$$(\mathbf{r}) = \frac{1}{\mathbf{p} - \mathbf{e}^{ik_{jj}r_{jj}}} \mathbf{k}_{z} (\mathbf{z})$$
(21)

where,  $k_z$  (z), is the perpendicular part of the full wavefunction. Sates above the vacuum are normalized to the volume = L<sup>3</sup> while states below it are normalized to = a<sup>3</sup>.

B. T ip and adsorbate wavefunctions

The adsorbate wavefunction is described using a Slater-type function:

$$_{i}(\mathbf{r}) = N_{i}\mathbf{r}^{n-1} e^{-i\mathbf{r}}Y_{lm} (; );$$
 (22)

where n is the main quantum number, l the angular momentum and m the z-component of the angular momentum. The normalization constant of orbital i is N<sub>i</sub> =  $[(2n)!]^{1=2} (2_i)^{(n+1=2)}$  and Y<sub>lm</sub> (;) is a conventional spherical harmonic. For the 3d transition metal atom we use n = 3;l = 2;m = 0 with an exponential decay  $_d = 2:3a_0^{-1}$ , where  $a_0$  is the Bohr radius.

Following Terso and H am ann,<sup>18</sup> the tip wavefunction,  $\pm$ >, is described by a simple stype orbital (n = 1), with an exponential decay <u>xed</u> by the workfunction of the m etal surface:  $_{t} = 2m_{e}W = h^{2}$ , where  $m_{e}$  is the electron m ass and W is the workfunction of the m etal surface which we take to be W = 4.95 eV in our calculations. This choice for  $_{t}$  relies on the fact that, typically, tungsten tips are dipped in them etal surface beforem easuring the conductance between the STM tip and the surface.<sup>9</sup> H ence, it is reasonable to describe the wavefunction tails sticking out from the tip with the same exponential decay as the ones describing the m etal surface.

# C.Computation of matrix elements

Once we have obtained the wavefunctions of the substrate we may proceed with the computation of the hybridization and overlap matrix elements de ned in Eq. (11). For simplicity we discuss the adsorbatesubstrate hybridization matrix elements. From Eq. (21) hybridization and overlap matrix elements expressed in cylindrical coordinates, read:

$$\begin{array}{rcl}
& Z_{1} & Z_{1} \\
V_{k} &= 2 & dr_{jj}r_{jj} & dz_{k_{z}}(z)J_{0}(k_{jj}r_{jj})V_{M}(z)_{d}(jr & r_{d}) \\
& Z_{1}^{0} & Z_{1}^{0} \\
S_{k} &= 2 & dr_{jj}r_{jj} & dz_{k_{z}}(z)J_{0}(k_{jj}r_{jj})_{d}(jr & r_{d}) \end{array}$$

where  $J_0$  ( $k_{jj}r_{jj}$ ) is the cylindrical Bessel function of zeroth order,  $V_M$ , is the surface potential and d (jr rd j) is the adsorbate wavefunction. The computation of the tip-substrate hybridization matrix elements, M k, proceeds along similar lines replacing d (jr rd j) by t (jr R j).

The behavior of tip m atrix elements deserves careful attention. Due to the slow decay of the tip wave function, most of the contribution to M  $_{\rm K}$  comes from the region close to the metal surface for  $k_z$  not too large. M atrix elements M  $_{\rm K}$  (R ) can then be approximately factorized as  $^{10}$ :

$$M_{\kappa}(R) = f(Z_t)e^{ik_{jj}R_{jj}}M_{\kappa}^{*}$$
: (24)

where  $M_{R}$  is independent of the tip position. This remains true for  $k_z < 1:6 - 1:7 A^{-1}$ , which is close to  $k_0 = 1.85 A^{-1}$  (for  $V_0 = 13.05 eV$ ). The function f (Z<sub>t</sub>) is related to the value of the tip wave function in the surface region and it decays rapidly<sup>19</sup> with Z<sub>t</sub>.  $M_{R}$  is found to have a weak dependence on  $k_z$  in contrast to matrix elements obtained from the original substrate wavefunctions as can be observed in Fig. 3. Indeed, using  $V_M$  in the matrix elements as in posed by the orthogonalization cuts o part of the surface leading to a weaker dependence on  $k_z$ . This is crucial to obtain reasonable shapes of B (!).

In order to have a qualitative understanding of the behavior of adsorbate-substrate hybridization m atrix elem ents,  $V_k$ , we focus on electrons which have no parallel m om entum ,  $k_{ii} = 0$ . M atrix elem ents gradually increase with increasing  $k_z$  due to increasing overlap of the metal states with the adsorbate. The behavior of matrix elem ents at large kz can be partially understood by analyzing Eq. (23) with  $k_z$  (z) nearly constant, (which is the case for the m etalwavefunction outside the surface). For a  $d_{3z^2 r^2}$  adsorbate the associated m atrix elements,  $V_{p}$ would tend to zero due to cancellations associated with the lobes of the 3d-orbital. Indeed, we nd that while V<sub>r</sub> computed for a d-orbital presents a downturn at in-1:4 A  $^1$  , V  $_{\rm K}$  computed with an s-type term ediate k<sub>z</sub> orbital increases rapidly up to  $k_z = k_0 \cdot 0$  rthogonalization e ects are also in portant as can be noticed from the fact that  $V_k < d \mathbf{y}_M \mathbf{j} d > S_k$  as  $k_z \mathbf{k}_0$ . Hence, we

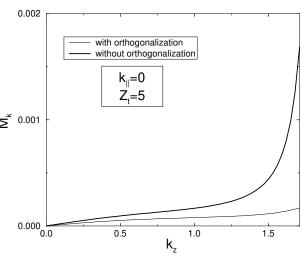


FIG.3: E ect of orthogonalization on tip-substrate hybridization m atrix elements. W hile hybridization m atrix elements computed between the original substrate wavefunctions and the tip depend strongly on perpendicular m on entum,  $k_z$ , this dependence is weaker form atrix elements containing orthogonalization corrections. The JJJ potential used in this calculation is parameterized using = 1:7 A<sup>-1</sup>, V<sub>0</sub> = 13:05 eV, and Z<sub>im</sub> = 1:1 A. The tip is located at Z<sub>t</sub> = 5 A above the surface plane of ions on top of the adsorbate (R<sub>jj</sub> = 0).  $k_z$  is given in A<sup>-1</sup> with the vacuum level corresponding to  $k_0 = 1:85$  A<sup>-1</sup>.

nd that matrix elements computed using orthogonalized wavefunctions,  $V_{\rm g}$ , initially increase with  $k_z$ , reach a maximum and then they are gradually suppressed regardless of the angular dependence of the adsorbate orbital. This dependence of  $V_{\rm g}$  is rejected in the frequency dependence of B (!). The above discussion illustrates the importance of appropriately including orthogonalization elects in the computation of hybridization matrix elements.

The behavior of matrix elements at very large perpendicular momentum needs to be carefully examined. M etallic waves with large m om entum (corresponding to energies far above the vacuum level), contain rapid oscillations which lead to cancellations in the integrand of Eq. (23). A high energy cut-o may be simply estimated from :  $k_i^{\text{cutoff}}$ i. This gives  $!_d^{cutoff}$ 70 eV for the adsorbate and  $!_t^{cutoff}$ 5 eV for the tip. Hence, hybridization matrix elements and in turn B (!) will be non-zero in the energy range  $V_0 < ! < !_t^{cutoff}$ . It is rem arkable that the tip cuts o all high energy contributions having an important in uence on the nalshape of B (!) and in turn on conductance lineshapes. This point seems to have been overlooked before.

D.Computation of B (!)

O noe we have the hybridization m atrix elements, it is straightforward, following Ref. [10] to obtain the energy dependence of B (!) given in Eq. (2). A fiter perform ing integration in parallelm om entum, B (!) can be written as

$$B (!) = -\frac{r}{\frac{2m_{e}^{3}}{h^{6}}(! + V_{0})} \int_{0}^{Z_{1}} dx V_{R_{jj};R_{z}} M_{R_{jj};R_{z}}; \quad (25)$$

where  $\tilde{k}_{jj} = \frac{q}{2m_e = h^2 (! + V_0)^p 1 x^2}$  and  $\tilde{k}_z = q$ 

 $2m_e = h^2 (! + V_0)x$  and is the volum e. N ote the factor appearing in front of the integral cancels out the volum e com ing from the norm alization of the surface wavefunctions com ing in the matrix elements.

### E.Param etrization of adsorbate G reens function

In order to com pute the modi cation induced by the adsorbate on conductance lineshapes, (!), know ledge of G<sub>dd</sub>(!) is needed. We take parameters used by U jaghy et. al.<sup>7</sup> to model Co on Au:  $_{\rm K}$  = 3 meV,  $_{\rm d}$  = 0.84 eV, U = 2.8 eV, A<sub>K</sub> = T<sub>K</sub> = , A<sub>d</sub> = 0.45 and A<sub>U</sub> = 1 A<sub>d</sub> A<sub>K</sub> with the K ondo temperature xed at T<sub>K</sub> = 5 meV. A swe are particularly interested in what is happening close to the Ferm i energy (at energy scales of the order of T<sub>K</sub>) the relevant parameters to our calculations are T<sub>K</sub> and  $_{\rm K}$ . Hence, these are input parameters which could be obtained from other sources such as experimental data or ab initio density functional calculations. It is not the purpose of the present work to have a

rst-principles determ ination of K ondo tem peratures for di erent adsorbate/substrate system s but rather to have a qualitative understanding of conductance lineshapes.

#### IV. DISCUSSION OF RESULTS

In this section we show our main results and discuss their relevance to experiments. A positive Fano param eter q 0 is typically found in our calculations for param eters charaterizing the noble m etal surface, the adsorbate and their mutual interaction. We explore how lineshapes depend on the parameters characterizing the atom -surface interaction. These parameters are: the position of the tip  $R = (R_{ij}; Z_t)$ , the adsorbate-substrate distance, Zd, and the shape of the surface potential controlled by . As there is cylindrical symmetry in our model, our results only depend on the absolute magnitude of the tip-adsorbate lateral displacem ent  $R_{ij} = \Re_{ij}$ . We do not nd much dependence of our results with the workfunction or the height of the surface barrier so we x  $V_0 = 13.05 \text{ eV}$  and the work function W = 4.95 eV, which are typical values for noble m etal surfaces. W e will rst discuss the dependence of lineshapes with the tip xed on top of the adsorbate,  $R_{ij} = 0$  at a distance of about  $Z_t = 5 A \cdot At$  the end of the section we will study how lineshapes depend on R  $_{ii}$  and Z  $_t$ .

# A. Dependence of Fano lineshapes with adsorbate-surface distance

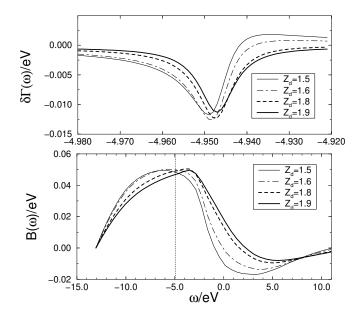
Fixing the tip at  $R_{ii} = 0$  (on top of the adsorbate) and  $Z_t = 5 A$  we analyze how lineshapes depend on the adsorbtion distance, Zd. In Fig. 4 the dependence of B (!) and (!) is shown for typical param eters describing noble m etal surfaces: 2:08 A  $^{1}$  , V<sub>0</sub> 13**:**05 eV at typical adsorbate-surface distances: Z<sub>d</sub> 1:5 2 A. Adsorbtion distances for di erent surfaces are obtained assuming hard spheres for the atoms. At large adsorbtion distances, Z<sub>d</sub> 2 A, B (!) is found to be rather symmetric with respect to the Fermi energy and consequently (see Fig. 2) the lineshape is a nearly symmetric dip. As the adsorbate is moved closer to the surface (Z<sub>d</sub> decreasing) the frequency dependence of B (!) varies and consequently the lineshapes too. An enhancem ent of weight below the Ferm i energy as well as a sharper drop above it occurs. This leads to a variation of lineshapes 0 at large distances towards q > 0 at short from q adsorbate-surface distances.

To understand these results, we notice that substrate states with low energy have a strong exponential decay outside the surface. As the adsorbate is brought closer to the surface, the overlap of the adsorbate orbital with these states increases. This leads to an increase of B (!) at sm all !. States with a larger energy extend farther outside the surface and have a substantial overlap with the di erent lobes of the adsorbate 3d-orbital. This tends to lead to a cancellation of the di erent contributions to  $V_k$ . This tendency increases as the adsorbate is brought closer to the surface, explaining the reduction of B (!) at larger !.

For comparison we also show in Fig. 5 the dependence of lineshapes with the adsorbate-surface distance for a Jellium with a step potential. Lineshapes are found to be som ewhat asym m etric as a large part of the weight in situated at low energies in B (!) (see also Fig. 1). A weaker dependence of B (!) with the adsorbate-surface distance is obtained as compared to the JJJ potential. The fact that we obtain reasonable lineshapes with a sim plem odel such as a Jellium with a step potential can be attributed to orthogonalization e ects. Tip-substrate m atrix elements computed without orthogonalization corrections would increase rapidly with  $k_z$  as they involve integrations over the whole space (instead of the region close to the surface) leading to rather asymmetric shapes of B (!).

# B. Dependence of lineshapes with the shape of the potential barrier

There are two parameters that can be tuned to change the shape of the surface potential. One is the image plane position,  $Z_{\rm im}$ , and the other is the sharpness of the surface potential given by . We x  $Z_{\rm im} = 1:1$  A and study the dependence of B (!) and lineshapes (!), with



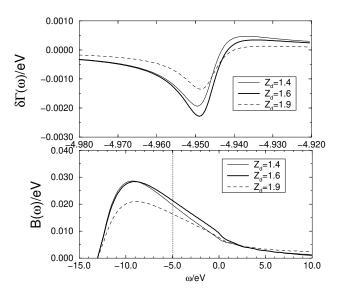


FIG.4: Dependence of lineshapes on the adsorbate m etal adsorption distance. As the adsorbate is brought closer to the surface the lineshapes become gradually m ore asymmetric. The lower pannel displays the function B (!) and in the upper one is the corresponding modi cation in the tip-surface interaction induced by the adsorbate: (!). The JJJ potential is parametrized using = 2:08 A<sup>-1</sup> and Z<sub>im</sub> = 1:1 A. The tip is located at Z<sub>t</sub> = 5 A above the surface plane of ions. All distances in the gure are given in A and refered to the last plane of ions. The vertical dotted line denotes the Ferm i level position:  $_{\rm F} = W = 4:95$  eV. The height of the surface barrier is V<sub>0</sub> = 13:05 eV.

the sharpness of the potential barrier. This dependence is shown in Fig. 6. We nd that an increase in leads to a more asymmetric B (!) and the associated conductance lineshape, (!) with more positive values of the Fano parameter, q.

Increasing makes the metal potential,  $V_{\rm M}$ , sharper so that the exponential tails of the metal wavefunctions outside the surface are shifted closer to the adsorbate leading to a stronger metal-adsorbate overlap. This is analogous to bringing the adsorbate closer to the surface for a xed

as discussed previously. Hence, an increase in leads to an increase in the weight of B (!) at low energies and a sharper drop at energies above the Ferm i level. The stronger dependence found for B (!) with than with the adsorbate-substrate distance can be ascribed to the exponential dependence of  $V_M$  with .

Sum m arizing, we nd that lineshapes are strongly dependent on the degree of sharpness of the m etal potential. M aking the surface potential sharper leads to m ore asym m etric lineshapes at typical atom -substrate adsorption distances.

FIG.5: Dependence of lineshapes on the adsorbate-m etal adsorption distance for a Jellium model with a step potential. In contrast to the JJJ model potential (see Fig. 4) there is a weak dependence of lineshapes with the adsorbate-substrate distance. The tip is located at  $Z_{\rm t}$  = 5 A above the surface plane of ions. All distances in the gure are given in A.The vertical dotted line denotes the Fermi level position:  $_{\rm F}$  = W = 4:95 eV.The height of the surface barrier is V<sub>0</sub> = 13:05 eV.

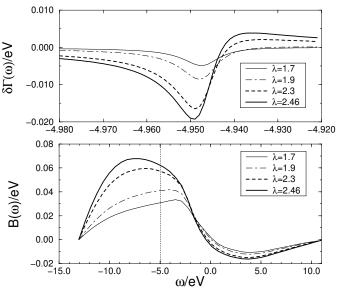


FIG.6: Dependence of lineshapes with the sharpness of the surface potential. As increases B(!) and lineshapes become m ore asymmetric. The lower pannel shows B(!) for dierent

and the upper one the corresponding lineshapes. The surface potentialism odelled for di erent and Z<sub>im</sub> = 1:1 A. The position of the tip and adsorbate are Z<sub>t</sub> = 5 A and Z<sub>d</sub> = 1:6 A, respectively. All distances are given in units of A and is in units of A<sup>-1</sup>. The vertical dotted line denotes the position of the Fermi level:  $_{\rm F}$  = W = 4:95 eV.

# ${\tt C}$ . Dependence of conductance lineshapes with tip position

We nally discuss the dependence of conductance lineshapes when the tip is moved away from the adsorbate either laterally ( $R_{jj} \notin 0$ ) or perpendicularly. The tip position comes into our calculations through matrix elements,  $M_{R}$ . A weak dependence of lineshapes with perpendicular tip-substrate distance,  $Z_{t}$  is found. Varying the distance from 5 to 7 A leads to a small change in the lineshape becoming slightly more asymmetric (see Fig. 7). The weak dependence of the line shape on the tipsurface distance can be understood from Eq. (24). This equation predicts a strong reduction of the amplitude of the conductance with vertical displacement of the tip

f  $(Z_t)^2$ , but no change in its shape. The weak dependence found is consistent with experimental observations which also indicate that the direct tip-adsorbate coupling is very small (as expected from the localized nature of the d-orbital of the adsorbate).

W e can also analyze how lineshapes depend on the lateral position of the tip, R<sub>jj</sub>. An example is shown in Fig. 7 which a rapid decay of the amplitude of the lineshapes is found. Lineshapes are found to depend slightly on R<sub>jj</sub> at tip-surface distances of about  $Z_t = 7$  A which is the typical experimental tip position. Indeed, crystal wavefunctions with  $k_{jj} = 0$  have the largest amplitude outside the surface representing electrons which have the largest probability of being detected by the tip (see R ef. [10] for discussion). Hence, the oscillatory behavior appearing in Eq. (24) is suppressed as only the states with sm all  $k_{jj}$  contribute to the momentum sum s.

The rapid decay of the am plitude with R<sub>jj</sub> obtained from our calculations is consistent with the disappearance of the features in the conductance at distances of about R<sub>jj</sub> 5 10 A. However, the sm all variation of the shape of the conductance with R<sub>jj</sub> found is only partially consistent with experiments as for some systems such as Co on Cu (100) or Co on Au (111) lineshapes becom e gradually more symmetric (q! 0) at larger R<sub>jj</sub>. It is worth mentioning that in the case of Co on Au (111), the lateral dependence of lineshapes depends not only on the modulus of R<sub>jj</sub> but also on the direction in which the tip is moved<sup>1</sup> from the adsorbate. This cannot be described in the present fram ework as the surface corrugation is not included in our model.

The nite size of the tip leads to a suppression of the tip-substrate m atrix elements at large energies due to rapid oscillations of the m etal wavefunctions providing a high energy cut-o. This cut-o turns out to be crucial to obtain reasonable lineshapes. Had we used a point-like tip the amplitude of B (!) at energies below the vacuum level would be exponentially suppressed while above it large oscillations would occur. This is because wavefunctions are evaluated far from the surface (at the tip position). Hence, for a point-like tip the Fano param eter would be very large (q >> 1) and a peak rather than a

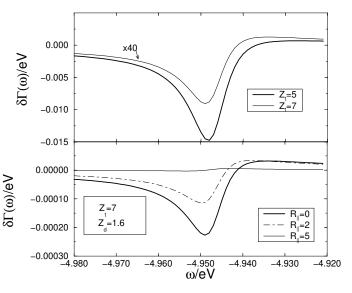


FIG.7: Dependence of lineshapes on the position of the tip. The upper panel shows the sm all perpendicular dependence of lineshapes if the tip is moved outwards from the surface by 2 A. The surface potential is parametrized by = 2:1 A<sup>-1</sup> and the position of the image plane  $Z_{\rm im}$  = 1:1 A. The adsorbate is at  $Z_{\rm d}$  = 1:6 A. All distances in the plot are given in A and the Fermi level is situated at:  $_{\rm F}$  = 4:95 eV. The conductance lineshape at  $Z_{\rm t}$  = 7 A is multiplied by 40 for comparison with  $Z_{\rm t}$  = 5 A.

dip would appear in conductance measurem ents.

# V. AN APPLICATION TO CONDUCTANCE MEASUREMENTS OF COBALT ON COPPER SURFACES

In the previous sections a detailed description of the m ethod used has been provided. In the following we provide the reader with an application to conductance m easurem ents of Cu surfaces with Co atoms deposited on them.

Copper surfaces are described using the parameters quoted in Ref. [17] for the analysis of surface states in noble m etal surfaces. For Cu surfaces we take = 22A  $^1$  and the adsorbate -substrate distance is estimated assuming hard spheres for the atom  $s^{20}$  As the (111) surface is more closely packed than the (100) surface the Co atom adsorbs at larger distances in the form er than in the latter surface. This leads to  $Z_d = 1.5 A$  and  $Z_d = 1.8$  A for the (100) and (111) surfaces, respectively. At the temperatures used in the experimental studies of the conductance,<sup>3</sup> C o sits outside the C u (100) surface and it is not incorporated in the surface, as happens at higher tem peratures<sup>21</sup>. Ab initio calculations<sup>22</sup> then give  $Z_d = 1.5 A$ , in agreem ent with our simple estimate. We nd that di erence in the adsorbtion distance is enough to produce changes in the lineshapes as can

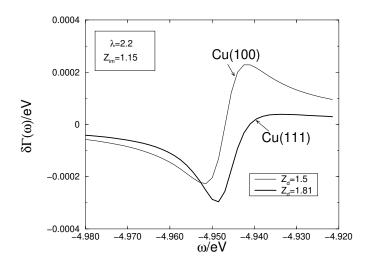


FIG. 8: Lineshapes associated with conductance measurements of C o on Cu (100) and Cu (111). Parameters taken from Ref. [17] are used to describe the surface potential: = 22 A<sup>-1</sup> and Z<sub>im</sub> = 1.15 A. The adsorbtion distance is larger for Cu (111) than Cu (100) by about 0.3 A. This leads to a more asymmetric lineshape in the latter than in the former case in agreement with experimental indings.<sup>3</sup> All distances in the gure are given in A and is given in A<sup>-1</sup>.

be observed in Fig. 8. From the dependence of lineshapes with  $Z_d$  discussed above we nd that for Co on Cu (100) surfaces lineshapes would be more asymmetric than for Co on Cu (111). This is consistent with experiments performed for these two dimenst surfaces.<sup>3,23</sup> Our result may be of more general validity and may apply to conductance measurements on other metal surfaces such as Ag or Au. However, care should be taken as our model contains the adsorbate-substrate distance only: corrugation e ects may also be important. More experiments that system atically analyze the dependence of lineshapes for Co on dimenstrate for corroborate our notings.

### VI. CONCLUSIONS

W e have introduced an Anderson m odel in an appropriate orthogonalized basis to analyze STM m easurements of noble m etal surfaces with adsorbed transition m etal atom s. A realistic surface potential (JJJ potential), a single  $d_{3z^2 r^2}$  adsorbate orbital and a stip orbital are used to compute the parameters of the m odel.

For typical values of the param eters characterizing the adsorbate-substrate interaction, we nd lineshapes with Fano param eters, q = 0, in agreem ent with experim ental trends.

We have introduced a function B (!) which describes the adsorbate-substrate interaction. The description of experim ental observations requires a B (!) which is fairly symmetric with respect to the Fermi energy. Since the underlying density of states is approximately parabolic and the matrix elements tend to further reduce B (!) at small !, it is interesting that the model, nevertheless, gives reasonable shapes for B (!). We nd that the tip matrix elements play an important role. The tip wave function is rather extended, and m atrix elements to continuum states at high energies are very small, due to the rapid oscillations of the continuum states over the spatial range of the tip wave function. This helps to make B (!) more symmetric around ! = F. We also not that it is essential to use substrate states which have been orthogonalized to the adsorbate and the tip. Even when the realistic JJJ potential is used, lineshapes are found to strongly depend on the sharpness of the surface potential controlled by becoming more asymmetric with (i. e. for sharper potentials). To a lower increasing degree conductance lineshapes are also found to depend on the adsorbtion distance: the closer to the surface the adsorbate is the more asym metric the lineshapes become. These tendencies can be explained from the enhancem ent in the coupling of the metal wavefunctions and the adsorbate at low energies together with the suppression at energies above the Ferm i level induced by the angular dependence of the  $d_{3z^2}$  r<sup>2</sup> orbital and the orthogonalization.

M ore closely packed surfaces such as Cu(111) are expected to lead to more symmetric lineshapes than the more open Cu(100) faces as Co adsorbs further out in the former than in the latter. We nd good agreement with experiments comparing lineshapes of Co on Cu(100) with Co on Cu(111) surfaces. In agreement with experiments we also nd that the tip-substrate distance does not strongly in uence the shape of the conductance.

### A cknow ledgm ents

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- $^{\rm 23}$  As this paper was in the nishing stage, a preprint by Lin, Castro-Neto and Jones (LCJ)<sup>24</sup> appeared, which addresses sim ilar problem s as the present paper. O ne di erence between the two approaches is that non-orthogonality between the substrate, adsorbate and tip orbitals has been neglected in LCJ as is typically done in related works using the Anderson ham iltonian. However, we nd that orthogonalization has important e ects on tip matrix elements as shown in Fig. 3. By including orthogonalized substrate orbitals we nd that lineshapes at R <sub>jj</sub> = 0 and their dependence with the tip position are in good agreem ent with experim ental observations unlike in LCJ who have to introduce an energy cut-o of 0.25 eV above the Ferm i energy in order to explain the lineshapes of Co on Cu (100). On the other hand for the case of Co on Cu (111) LCJ have included both bulk and surface states in their calculations while we consider bulk states only.
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